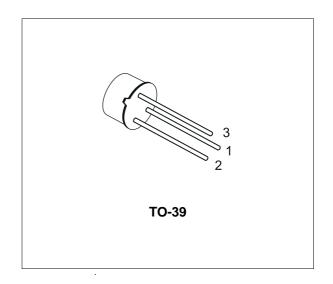


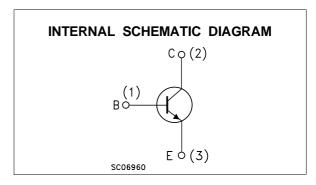
EPITAXIAL PLANAR NPN

DESCRIPTION

The 2N1711 is a silicon Planar Epitaxial NPN transistor in Jedec TO-39 metal case. It is intented for use in high performance amplifier, oscillator and switching circuits.

The 2N1711 is also used to advantage in amplifiers where low noise is an important factor.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage (I _E = 0)	75	V
VCER	Collector-Emitter Voltage ($R_{BE} \le 10\Omega$)	50	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	7	V
Ic	Collector Current	500	mA
P _{tot}	Total Dissipation at $T_{amb} \le 25$ °C at $T_C \le 25$ °C at $T_C \le 100$ °C	0.8 3 1.7	W W W
T _{stg}	Storage Temperature	-65 to 175	°C
Tj	Max. Operating Junction Temperature	175	°C

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THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-Case	Max	50	°C/W
$R_{thj-amb}$	Thermal Resistance Junction-Ambient	Max	187.5	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

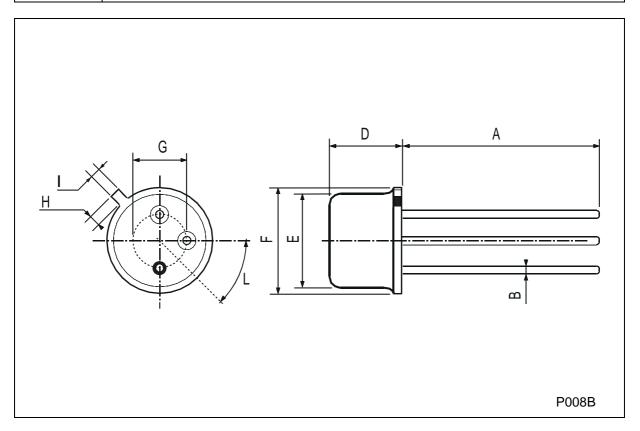
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit	
I _{CBO}	Collector Cut-off Current (I _E = 0)	V _{CB} = 60 V V _{CB} = 60 V T _C = 150 °C			10 10	nΑ μΑ	
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			5	nA	
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage (I _E = 0)	I _C = 100 μA	75			V	
V _(BR) CER*	Collector-Emitter Breakdown Voltage $(R_{BE} \le 10\Omega)$	I _C = 10 mA	50			V	
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = 100 μA	7			V	
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 150 mA I _B = 15 mA		0.5	1.5	V	
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 150 mA I _B = 15 mA		0.95	1.3	V	
h _{FE} *	DC Current Gain	$\begin{array}{llllllllllllllllllllllllllllllllllll$	20 35 75 100 40	60 80 130 130 75	300		
h _{fe}	Small Signal Current Gain	I _C = 1 mA V _{CE} = 10 V f = 1 KHz	70	135	300		
f_{T}	Transition Frequency	$I_C = 50 \text{ mA} \text{ V}_{CE} = 10 \text{ V} \text{ f} = 20 \text{ MHz}$	70	100		MHz	
СЕВО	Emitter-Base Capacitance	$I_{C} = 0$ $V_{EB} = 0.5 \text{ V } f = 1 \text{ MHz}$		50	80	pF	
Ссво	Collector-Base Capacitance	I _E = 0 V _{CB} = 10 V f = 1 MHz		18	25	pF	
NF	Noise Figure	$I_C = 0.3 \text{ mA}$ $V_{CE} = 10 \text{ V}$ $R_g = 510 \Omega$ $f = 1 \text{ KHz}$		3.5	8	dB	
h _{ie}	Input Impedance	$I_C = 1 \text{ mA}$ $V_{CE} = 5 \text{ V}$ $f = 1 \text{ KHz}$		4.4		ΚΩ	
h _{re}	Reverse Voltage Ratio	$I_C = 1 \text{ mA}$ $V_{CE} = 5 \text{ V}$ $f = 1 \text{ KHz}$		7.3 x 10 ⁻⁴			
hoe	Output Admittance	$I_C = 1 \text{ mA}$ $V_{CE} = 5 \text{ V}$ $f = 1 \text{ KHz}$		23.8		μS	

^{*} Pulsed: Pulse duration = 300 μs, duty cycle ≤ 1 %

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TO-39 MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	12.7			0.500			
В			0.49			0.019	
D			6.6			0.260	
Е			8.5			0.334	
F			9.4			0.370	
G	5.08			0.200			
Н			1.2			0.047	
I			0.9			0.035	
L	45° (typ.)						



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